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A Review on the Application Potential and Challenges of Carbon-based Nanomaterials in Novel Integrated Circuit Modules

Yihuai Bi

School of Microelectronics, South China University of Technology, Guangzhou, China
15163477778@163.com

Abstract. With the rapid development of semiconductor technology, traditional silicon-based integrated circuits are gradually approaching fundamental physical limits, including short-channel effects, quantum tunneling and thermal dissipation bottlenecks, which have significantly slowed down the pace of Moore's Law. Carbon-based nanomaterials, primarily graphene and carbon nanotubes, have emerged as ideal candidate materials for next-generation integrated circuit modules due to their outstanding electrical, thermal and mechanical properties. This paper employed a systematic literature review to examine the fundamental characteristics and mainstream synthesis methods of carbon-based nanomaterials, with a focus on their latest application in transistors, interconnection lines, thermal management and other key modules. This paper further analyzed the key technical bottlenecks and industrialization challenges in practical implementation. The results showed that carbon-based nanomaterials have significant application potential for high-performance and low-power integrated circuits, while critical issues such as large-scale uniform preparation, precise interface control, and compatibility with existing silicon-based processes remain to be addressed.

Keywords: Carbon-based nanomaterials, Integrated circuits, Graphene, Carbon nanotubes, Semiconductor materials

1. Introduction

The continuous miniaturization and performance improvement of integrated circuits are the core driving forces of the information industry. However, the short channel effect, heat dissipation and integration bottlenecks of silicon-based devices restrict the further development of traditional semiconductor technology [1]. Carbon-based nanomaterials have attracted extensive attention in the field of microelectronics due to their high carrier mobility, high thermal conductivity and atomic thickness [2]. At present, scholars at home and abroad have carried out a lot of research on the preparation, characterization and device application of carbon-based nanomaterials, and achieved phased results in laboratory-level integrated circuit modules [3, 4]. This paper adopts the methods of literature review and comparative analysis to sort out the research progress of carbon-based nanomaterials in new integrated circuit modules, clarify the main application scenarios and technical

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limitations, and discuss the existing challenges and solutions. This paper is structured as follows: first, it introduces the classification, structural characteristics, preparation processes and core properties of carbon-based nanomaterials; then, it reviews their applications and potential in core integrated circuit modules and post-Moore semiconductor technology. Subsequently, it analyzes the key technical bottlenecks and industrialization challenges hindering their large-scale practical application. Finally, this paper proposes targeted development strategies and gives a comprehensive outlook for future research directions and industrialization prospects. This study aims to provide some references for the design, preparation and industrialization of next-generation high-performance integrated circuit modules, and promote the application and development of carbon-based nanomaterials in the microelectronics industry.

2. Overview of carbon-based nanomaterials

2.1. Classification and structural characteristics

Graphene and carbon nanotubes serve as the two most typical carbon-based nanomaterials in microelectronic device applications, representing the two most extensively studied low-dimensional carbon allotropes with unique electronic structures. Graphene is a single-layer two-dimensional honeycomb lattice structured by sp^2-hybridized carbon atoms, where each carbon atom forms three σ bonds with adjacent atoms and one delocalized π bond perpendicular to the plane. This unique atomic arrangement endows graphene with ultrahigh carrier mobility above 200,000 $cm^2/(V \cdot s)$ at room temperature, as well as an atomic thickness of only 0.34 nm, making it the thinnest functional material ever discovered [5].

Carbon nanotubes are one-dimensional cylindrical nanostructures rolled from graphene monolayers, which can be classified into single-walled carbon nanotubes (SWCNTs) and multi-walled carbon nanotubes (MWCNTs) according to the number of graphene layers. Among them, SWCNTs possess superior ballistic transport behaviors and robust mechanical stability, enabling high carrier mobility retention even at room temperature without significant scattering [5]. Such structural characteristics grant both graphene and carbon nanotubes distinctive merits in device miniaturization and high-frequency working performance, as they can maintain excellent electronic properties even when scaled down to atomic dimensions.

2.2. Common preparation and transfer processes

Major fabrication approaches for carbon-based nanomaterials consist of mechanical exfoliation, chemical vapor deposition (CVD), epitaxial growth, and solution-based processing, each with distinct advantages and limitations. Mechanical exfoliation, the earliest method used to isolate single-layer graphene, enables the acquisition of high-purity graphene flakes with minimal structural defects and near-ideal electronic properties. However, this approach is inherently a manual, low-yield process that cannot satisfy the demands of large-scale industrial manufacturing [2]. Epitaxial growth on silicon carbide substrates can also produce high-quality graphene, but the high cost of substrates and the difficulty in transferring the grown films limit its widespread application.

At present, CVD represents the most feasible and scalable route to achieve wafer-scale material synthesis, where carbon-containing precursors are decomposed on catalytic metal substrates at high temperatures to form continuous graphene or carbon nanotube films. Nevertheless, significant challenges still exist in precisely controlling film thickness, grain size, and defect density over entire 8-inch or 12-inch wafers [3]. The transfer procedure, which involves detaching the grown films from

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the metal substrates and transferring them to target semiconductor substrates, exerts a direct influence on interface integrity and device performance. Hence, the development of low-damage and high-uniformity transfer techniques remains an essential prerequisite for the industrial implementation of carbon-based nanomaterials.

2.3. Key properties for integrated circuit applications

Carbon-based nanomaterials exhibit a suite of exceptional intrinsic properties that make them superior to conventional silicon-based materials for next-generation integrated circuits. In terms of electrical properties, their ultrahigh carrier mobility allows for faster carrier transport and higher operating frequencies, while their low intrinsic resistance reduces power consumption. In terms of thermal properties, monolayer graphene possesses a thermal conductivity reaching up to 5000 W/(m·K), which is more than ten times higher than that of copper, making it an ideal material for thermal management in high-density integrated circuits [2, 5].

In addition to their outstanding electrical and thermal properties, carbon-based nanomaterials also exhibit excellent mechanical flexibility and inherent atomic-scale thickness. Their mechanical flexibility allows them to be deposited on various flexible substrates, such as polymers and paper, supporting the development of flexible electronics and wearable devices. Their atomic-scale thickness, on the other hand, enables the fabrication of transistors with extremely short channel lengths, effectively suppressing the short-channel effects that plague conventional silicon-based devices as they scale down [6]. These unique characteristics collectively enable carbon-based nanomaterials to overcome the fundamental performance bottlenecks of conventional silicon-based materials, thus laying a robust physical foundation for the construction of high-frequency, low-power, and flexible integrated circuit modules.

3. Applications and potential of carbon-based nanomaterials in integrated circuits

3.1. High-performance logic and radio frequency devices

Transistors based on graphene and carbon nanotubes have demonstrated outstanding high-frequency operation capability and low-power consumption performance. For graphene-based transistors, a cutoff frequency exceeding 100 GHz has been successfully realized, which fully verifies their prominent application prospect in radio frequency front-end devices [3, 5]. Meanwhile, carbon nanotube field-effect transistors are capable of achieving ballistic transport under optimized operating conditions, and hold great promise for deployment in high-performance logic computing units [4, 7]. Such emerging device architectures offer an innovative technical route for the development of beyond-silicon integrated circuit systems.

Benefiting from their intrinsic ultrahigh carrier mobility and low scattering properties, carbon-based devices can achieve stable operation under high-frequency conditions and low driving voltages, realizing a simultaneous significant reduction in power consumption and marked enhancement in operating speed. These devices are well-suited for core chip applications in 5G/6G communication systems, radar front-end modules, and high-speed computing platforms, and exhibit prominent performance advantages over conventional silicon-based counterparts [2, 5]. As semiconductor technology advances into the post-Moore era, silicon-based devices are increasingly approaching fundamental physical limits, including short-channel effects and quantum tunneling effects [8]. Carbon-based nanomaterials are thus poised to serve as the core functional materials for beyond-silicon semiconductor technology, underpinning the sustained scaling of integration density

DOI: 10.54254/2755-2721/2026.AD33926

and device performance, and further driving the iterative upgrading of the entire semiconductor industry.

3.2. Interconnection and thermal management

As the integration density of chips continuously improves, conventional metal interconnects suffer from severe resistance-capacitance (RC) delay and heat dissipation issues, which have become major performance bottlenecks. Benefiting from their intrinsic low resistivity and ultrahigh thermal conductivity, carbon-based nanomaterials can effectively suppress interconnection delay and enhance thermal dissipation efficiency [6]. These materials have been widely deployed in on-chip local interconnections, thermal interface materials and heat dissipation channels, which effectively mitigate the critical thermal bottleneck restricting the development of high-density integrated circuit systems.

Three-dimensional (3D) integration technology boosts on-chip integration density through vertical multi-layer stacking, yet thermal management and interconnection performance have emerged as the primary bottlenecks restricting its large-scale deployment. Benefiting from their intrinsic ultrahigh thermal conductivity and outstanding interconnection characteristics, carbon-based nanomaterials can effectively mitigate the inherent heat accumulation and signal delay issues in 3D integration architectures, while simultaneously enhancing the long-term operational stability and energy efficiency of the entire integrated system [9].

3.3. Flexible electronics and 3D integration

Carbon-based nanomaterials exhibit good mechanical flexibility and can be deposited on flexible substrates, such as polymers, thereby supporting the development of flexible electronics, wearable devices and bendable chips. At the same time, they are compatible with heterogeneous integration processes and help realize three-dimensional integrated circuits with high efficiency and low power consumption [7].

Combined with their superior thermal and electrical interconnection properties mentioned above, carbon-based nanomaterials can solve the dual bottlenecks of heat dissipation and signal transmission in 3D stacked architectures, making them ideal functional materials for next-generation heterogeneous integrated systems [9].

4. Challenges to practical applications

4.1. Material synthesis and quality control

The wafer-scale fabrication of high-quality carbon-based nanomaterials with uniform properties serves as the cornerstone for their industrial application in integrated circuits. Chemical vapor deposition (CVD) has emerged as the most promising technique for large-area graphene synthesis, enabling the production of continuous films on metallic substrates. However, precise control over film thickness, grain size, and defect density across entire wafers remains a significant challenge, as even minor variations in growth conditions can lead to substantial performance discrepancies between devices fabricated on the same substrate [3]. For carbon nanotubes, the primary bottleneck lies in the selective synthesis of semiconducting nanotubes with uniform chirality, as metallic nanotubes present in the mixture can cause short circuits and degrade the performance of logic circuits [7].

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Mechanical exfoliation, while capable of producing defect-free graphene flakes with exceptional electronic properties, is inherently a low-yield, laboratory-scale process that cannot meet the demands of mass manufacturing [2]. Current CVD-grown materials typically contain a high density of intrinsic defects such as vacancies, grain boundaries, and unintentional dopants, which significantly reduce carrier mobility and increase device-to-device variability. These quality issues directly impact the fabrication yield of integrated circuits, making it difficult to achieve the high levels of uniformity required for commercial semiconductor production.

4.2. Interface engineering and process compatibility

The heterogeneous interface between carbon-based nanomaterials and conventional semiconductor materials represents one of the most critical technical hurdles in device fabrication. At the contact interface between carbon nanotubes or graphene and metal electrodes, the formation of Schottky barriers and the presence of interfacial defects lead to excessively high contact resistance, which severely limits the on-current and switching speed of field-effect transistors [4, 5]. Additionally, interfacial scattering caused by surface roughness and adsorbed contaminants further degrades carrier transport properties, preventing carbon-based devices from achieving their theoretical performance limits.

Another major challenge is the incompatibility between carbon-based nanomaterial processing and traditional complementary metal-oxide-semiconductor (CMOS) manufacturing flows. High-temperature processes commonly used in CMOS fabrication, such as thermal oxidation and dopant activation, can cause structural damage to carbon-based materials and degrade their electronic properties [8]. Furthermore, the introduction of carbon-based materials into existing fabrication lines raises concerns about cross-contamination, which could adversely affect the performance of silicon-based devices. Achieving seamless monolithic integration of carbon-based components with silicon CMOS platforms will require the development of low-temperature processing techniques and contamination control strategies.

4.3. Reliability and stability

The long-term reliability of carbon-based electronic devices remains a significant concern for practical applications. Carbon-based nanomaterials are highly sensitive to environmental conditions, with exposure to moisture and oxygen leading to the adsorption of molecules on their surfaces. These adsorbed molecules act as dopants or scattering centers, causing shifts in threshold voltage, reductions in carrier mobility, and gradual degradation of device performance over time [9]. This environmental sensitivity necessitates the development of robust encapsulation techniques to protect carbon-based devices from ambient conditions.

In addition to environmental stability, carbon-based devices also exhibit reliability issues under electrical bias stress. Prolonged operation under high electric fields can lead to the migration of metal atoms from electrodes into the carbon-based channel, the formation of defects in the material structure, and the degradation of interfacial properties. These effects result in a gradual decrease in device performance and a reduction in operational lifetime. While significant progress has been made in improving device stability through material engineering and encapsulation, further research is needed to ensure that carbon-based integrated circuits can meet the stringent reliability requirements of commercial electronic systems [9].

DOI: 10.54254/2755-2721/2026.AD33926

5. Development strategies and future outlook

5.1. Optimization of material preparation and purification technology

Efforts should be devoted to developing cost-effective, wafer-scalable and highly uniform CVD synthesis techniques, enhancing defect management and material purification, as well as elevating material quality and homogeneity to satisfy the demands of industrialized manufacturing [3, 7].

5.2. Innovation of device structure and integration process

Targeted implementations of interface engineering should be conducted to refine electrode contact architectures, suppress contact resistance, and reduce interfacial defects. Low-temperature compatible manufacturing processes should be developed to enable seamless monolithic integration with silicon-based CMOS platforms [5].

5.3. Future research directions and application scenarios

Subsequent research endeavors will center on high-efficiency logic components, radio frequency functional modules, flexible electronic systems and three-dimensional integrated architectures. As critical technological obstacles are surmounted, carbon-based nanomaterials are anticipated to achieve incremental application in advanced integrated chips, thereby fueling the long-term sustainable advancement of the integrated circuit sector [8, 9].

6. Key challenges in practical applications

6.1. Large-area high-quality preparation and uniformity control

The wafer-scale fabrication of carbon-based nanomaterials is the fundamental prerequisite for industrial implementation. These materials must have high uniformity and low defect density across the entire wafer. At the current stage, precise control of large-area material growth remains inadequate. Even small variations in growth conditions can cause significant differences in material properties.

Native defects and unintentional impurities directly degrade the electrical performance of fabricated devices. They also reduce the fabrication yield of integrated circuits. For carbon nanotubes, the selective synthesis of semiconducting nanotubes with uniform chirality remains a major challenge. These issues ultimately impose severe constraints on large-volume commercial manufacturing [3, 7].

6.2. Interface defects and contact resistance issues

The heterogeneous interface between carbon-based nanomaterials and metal electrodes is a critical factor affecting device performance. Inherent interfacial defects are inevitable during the fabrication process. Excessive contact resistance is another persistent problem at these interfaces.

These issues directly trigger marked degradation of device electrical performance. They also cause a notable rise in operating power consumption. Targeted regulation of interface engineering is urgently needed. Structural optimization of contact systems also remains a core technical hurdle in practical device manufacturing [5].

DOI: 10.54254/2755-2721/2026.AD33926

6.3. Compatibility with traditional silicon-based processes

Fabrication schemes for carbon-based nanomaterials differ substantially from conventional CMOS manufacturing flows. This incompatibility is one of the biggest barriers to industrial adoption. High-temperature processes in CMOS fabrication can cause structural damage to carbon-based materials. They also degrade the electronic properties of these materials.

Contamination management is another critical concern. The introduction of carbon-based materials may contaminate existing silicon fabrication lines. Further improvements are required in process matching to achieve seamless co-integration with silicon-based platforms [7, 8].

6.4. Stability and reliability in service

Carbon-based electronic devices are highly sensitive to ambient parameters. Moisture and oxygen exposure can cause gradual degradation of device performance. Adsorbed molecules on the material surface act as scattering centers and dopants. They shift the threshold voltage and reduce carrier mobility.

Electrical bias stress also compromises the long-term operational durability of devices. Prolonged operation under high electric fields can induce structural defects. Device reliability in practical service environments still demands extensive experimental validation. Corresponding encapsulation and protective strategies require further optimization and advancement [9].

7. Conclusion

This paper systematically reviews the fundamental characteristics, preparation methods and application progress of carbon-based nanomaterials in integrated circuits. Graphene and carbon nanotubes show outstanding advantages in carrier mobility, thermal conductivity and atomic-scale dimensional scaling. They can effectively break through the core bottlenecks of traditional silicon-based integrated circuits, and have broad application prospects in high-frequency electronics, flexible devices and 3D integrated systems.

However, the industrialization of carbon-based nanomaterials still faces multiple key challenges. These include large-scale uniform material preparation, high contact resistance at heterogeneous interfaces, poor compatibility with existing CMOS processes, and insufficient long-term service stability. This study also has certain limitations. It lacks in-depth experimental verification and only focuses on the two most mainstream carbon-based nanomaterial systems.

In the future, research should focus on three core directions. First, develop low-cost and high-quality wafer-scale material fabrication technologies. Second, optimize interface engineering and device structure design. Third, realize seamless compatible integration with silicon-based processing flows. With the continuous breakthrough of key technologies, carbon-based nanomaterials are expected to become the core materials of next-generation integrated circuits and promote the iterative upgrading of the semiconductor industry.

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